

TO-220F Plastic-Encapsulate MOSFETS

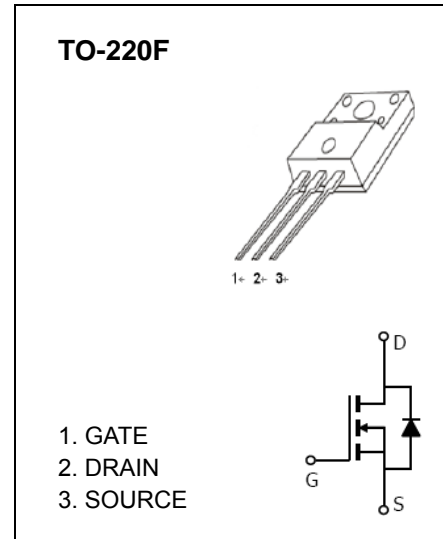
CJPF04N80 N-Channel Power MOSFET

GENERAL DESCRIPTION

This is a N-channel mode power MOSFET using advanced technology to provide planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance, and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode. It is universally applied in high efficiency switch mode power supply.

FEATURE

- High Current Rating
- Lower $R_{DS(on)}$
- Lower Capacitance
- Lower Total Gate Charge
- Avalanche Energy Specified
- High Switching Speed



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current	I_D	4.0	A
Pulsed Drain Current	I_{DM}	16	
Single Pulsed Avalanche Energy (note1)	E_{AS}	170	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	
Maximum lead temperature for soldering purposes , 1/8"from case for 5 seconds	T_L	260	

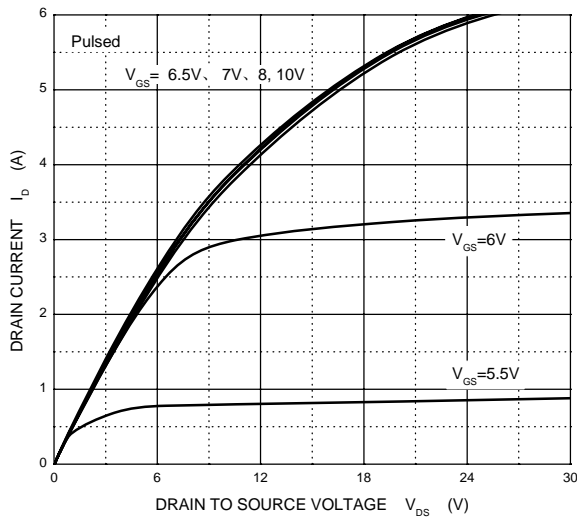
Electrical characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 800V, V_{GS} = 0V$			10	μA
Gate-body leakage current (note2)	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 30V$			± 100	nA
On characteristics (note2)						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3		5	V
Static drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2.0A$			3.0	Ω
Dynamic characteristics (note 3)						
Input capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$			880	pF
Output capacitance	C_{oss}				100	
Reverse transfer capacitance	C_{rss}				12	
Switching characteristics (note 2,3)						
Total gate charge	Q_g	$V_{DS} = 640V, V_{GS} = 10V, I_D = 4.0A$			25	nC
Gate-source charge	Q_{gs}			4.2		
Gate-drain charge	Q_{gd}			9.1		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400V, V_{GS} = 10V, R_G = 25\Omega, I_D = 4.0A$			40	ns
Turn-on rise time	t_r				100	
Turn-off delay time	$t_{d(off)}$				80	
Turn-off fall time	t_f				80	
Source-drain diode characteristics						
Maximum diode forward continuous current	I_S				4	A
Maximum diode forward pulse current	I_{SM}				16	A
Diode forward voltage	V_{SD}	$I_S = 4A, V_{GS} = 0V$			1.4	V

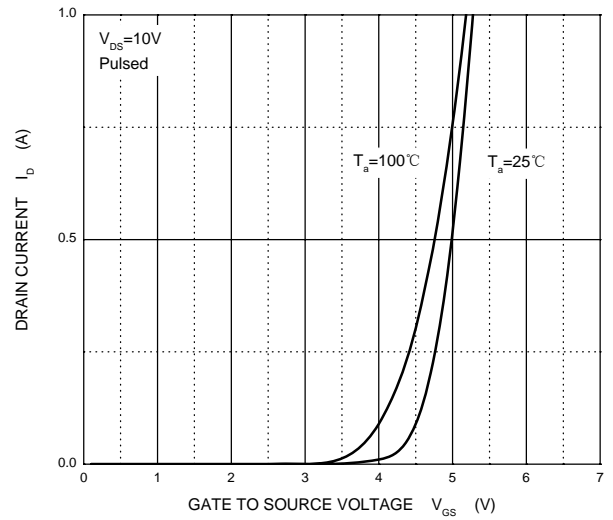
Notes :

- $L=20mH, I_L=4 A, V_{DD}=50V, V_{GS}=10V, R_G=25\Omega, \text{Starting } T_J=25^{\circ}\text{C}.$
- Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- These parameters have no way to verify.

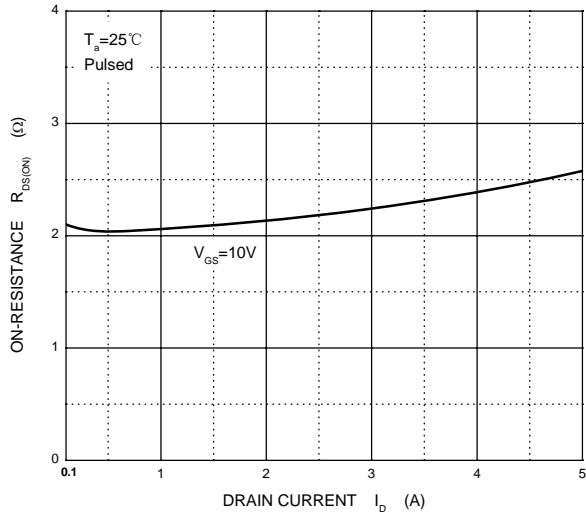
Output Characteristics



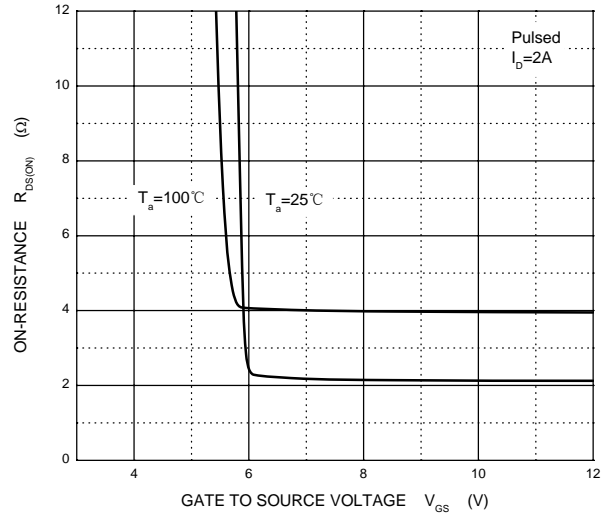
Transfer Characteristics



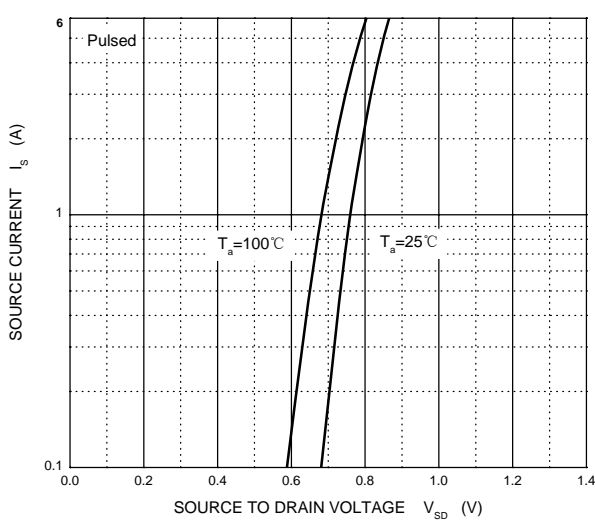
$R_{DS(ON)}$ — I_D



$R_{DS(ON)}$ — V_{GS}



I_S — V_{SD}



Threshold Voltage

